2SB647(A)

Rev.E Mar.-2016

DATA SHEET

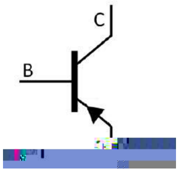
WR0<50P　ṂṂȽ SQS ᴁṀɥ s ǁ ᒣ　Silicon PNP transistor in a TO-92LM Plastic Package.

љ 5VG99 : +D, Йˏ ˊ

Complementary pair with 2SD667(A).

ኚ Ḩ ḽ ı ' ῷ ⁷

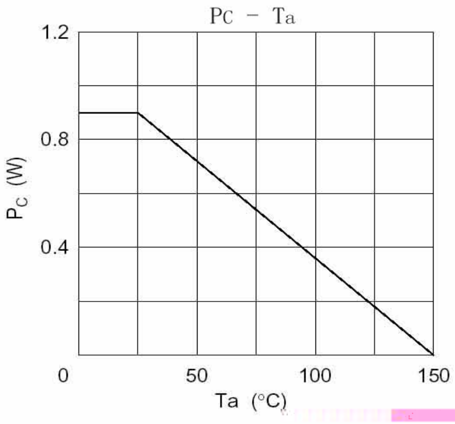
Low frequency power amplifier.

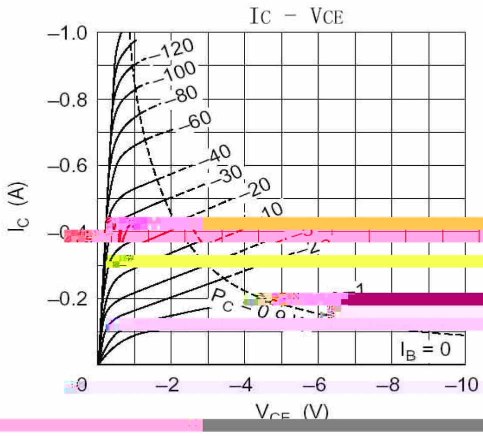


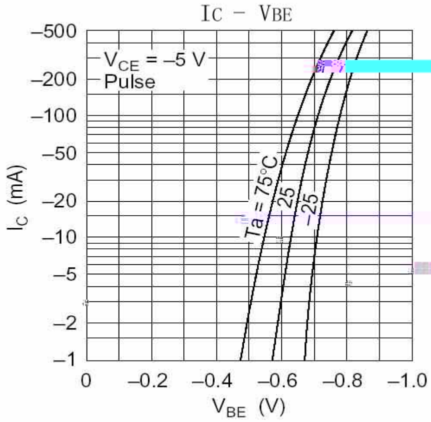
PIN1 χ Base　　PIN 2 χ Collector　　PIN 3 χ Emitter

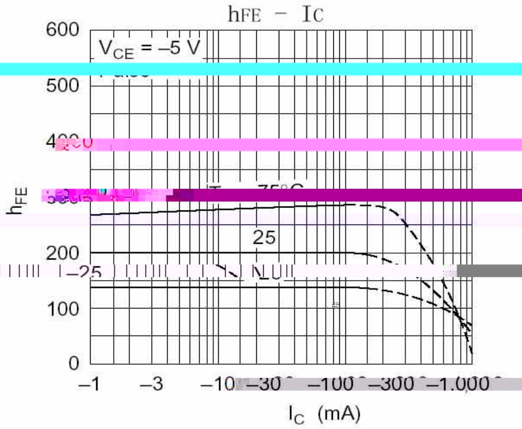
v ̋Ω̦ Parameter	ɻ ᴺ Symbol		̋Ω̦Ӫ Rating	ᴅ Ʉ Unit
Collector to Base Voltage	V_{CBO}		-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647	-80	V
		2SB647A	-100	
Emitter to Base Voltage	V_{EBO}		-5.0	V
Collector Current (DC)	I_C		-1.0	A
Collector Current(Pulse)	I_{CP}		-2.0	A
Collector Power Dissipation	P_C		900	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T			

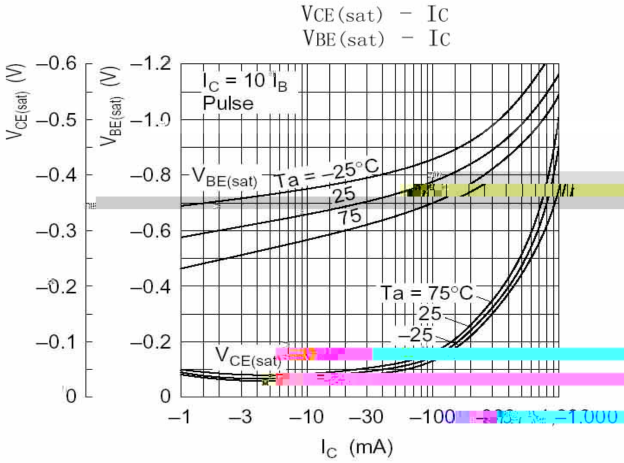
/ Electrical Characteristic Curve

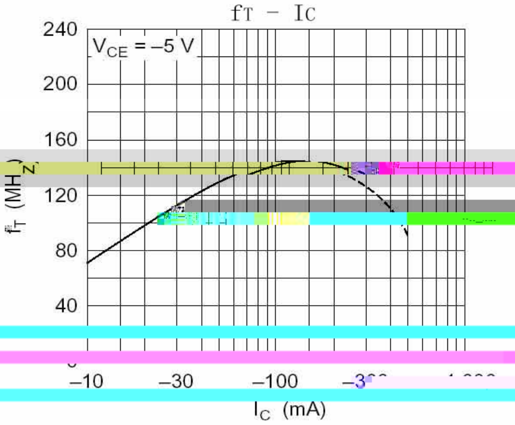




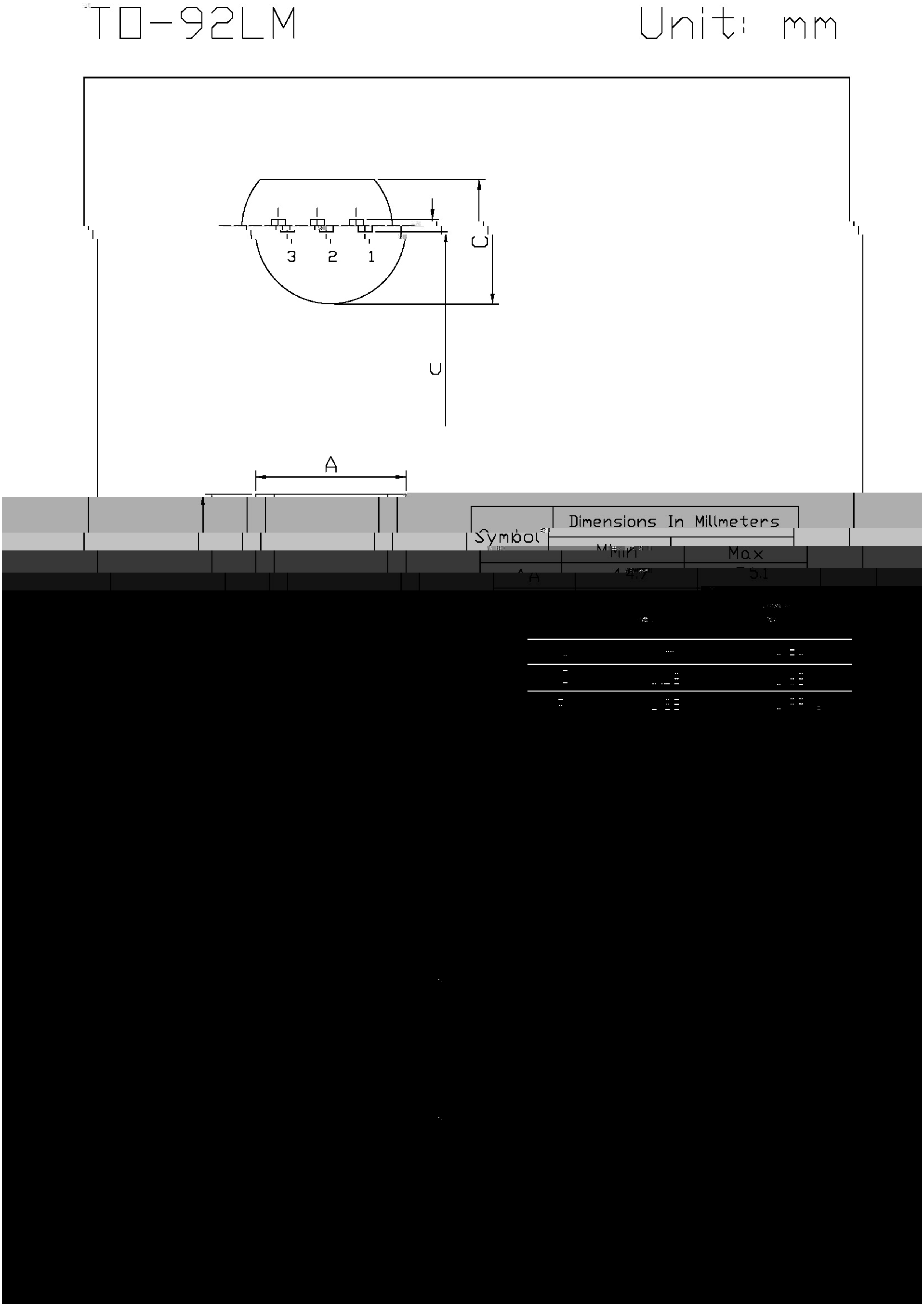






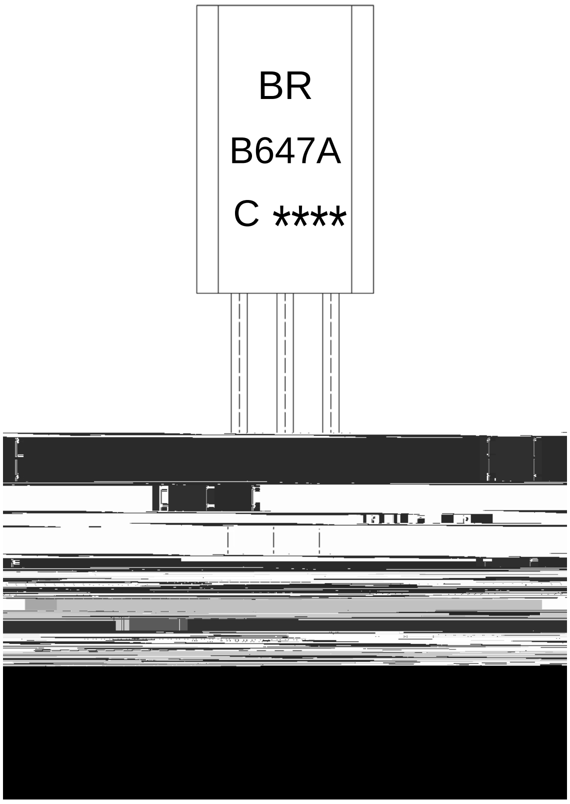


/ Package Dimensions



Symbol	Dimensions In Millmeters	
	Min	Max
A	4.7	5.1

/ Marking Instructions



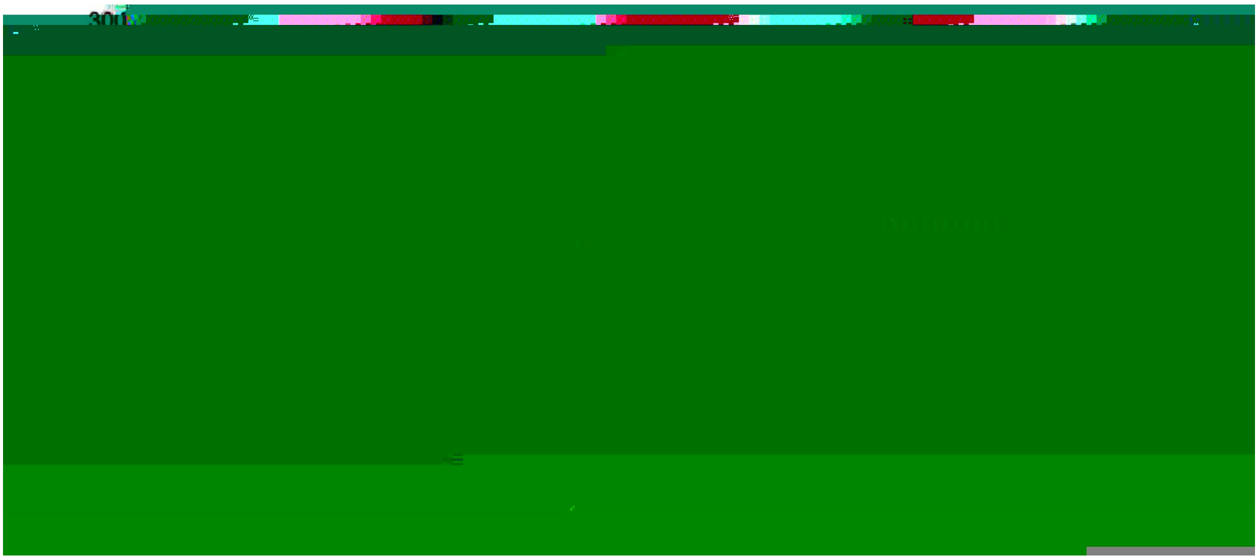
ب ˝ χ

EU꞉	ҥѫ ɿ ᴻ Ꞃƀ
E97 : D χ	ҥѫ ʒ ᴺ Ꞃƀ
F꞉	ҥѫ k IH ˂ ⁶ Ꞃƀ
- - - - χ	ҥѫ ˙ł ғ ή ᴺ Ꞃƀ ɩ ɞ ˙ł ғ ή ᴺ ψ ק

Note:

BR:	Company Code.
B647A:	Product Type.
C:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

(　　) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 ỉ ♬ □ ỹ 25 Ḱ 150 ƚ ı `H ڑ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ƚ